迈诺斯科技

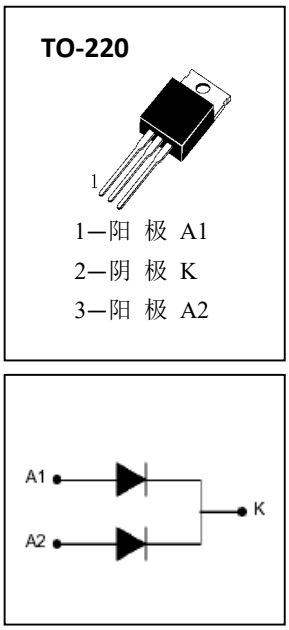
MBR20100CT

POWER SCHOTTKY BARRIER RECTIFIER

■ 主要用途

低压高频逆变电路，续流电路和保护电路等。

■ 外形图及引脚排列



■ 极限值（Ta=25℃）

T_{stg} —— 贮存温度..... 65 ~ 175 ℃

T_j ——结温..... -65 ~ 150 ℃

V_{RRM} —— 最大反向重复峰值电压..... 100V

V_{RWM} —— 反向峰值工作电压..... 100V

$V_{R(RMS)}$ —— 反向工作电压(RMS)..... 70V

V_R ——最大直流反向电压..... 100V

$I_{F(AV)}$ ——最大正向平均电流（Tc=125℃）..... 整个器件 20A

单个器件 10A

■ 电参数（Ta=25℃）

参数符号	符 号 说 明	最小值	典型值	最大值	单 位	测 试 条 件
I_R	反向瞬态电流			0.15 150	mA	$V_R=V_{RRM}$，T_C = 25 °C T_C=125°C
V_F	正向瞬态峰值压降 （注 1）			0.85 0.75 1.02 0.85	V	I_F=10 A，T_C=25°C I_F=10 A，T_C=125°C I_F=20 A，T_C=25°C I_F=20 A，T_C=125°C
$R_{th(j-c)}$	结到每只管脚的典型热阻			2.0	℃/W	结到每只管脚
C_j	结电容(注 2)			1000	pF	
$d_{V/dt}$	电压上升率			10000	V/μs	

注 1： 脉冲测试，脉冲宽度 300μS，占空比 2%。

注 2： 测试条件 f= 1MHz V_R=4V。

■ 特性曲线

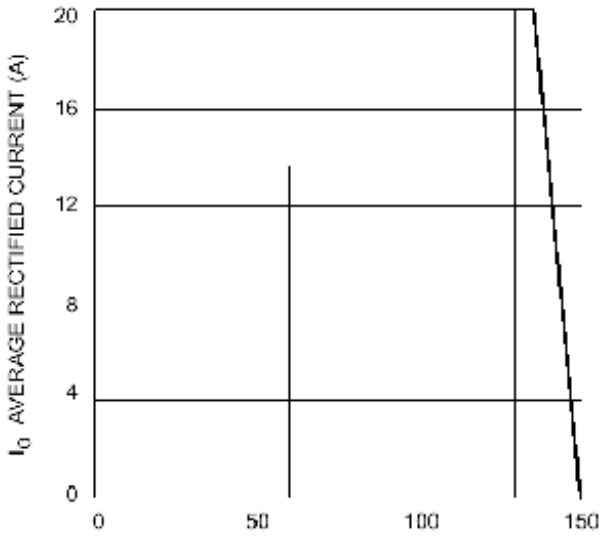


Fig. 1 Fwd Current Derating Curve

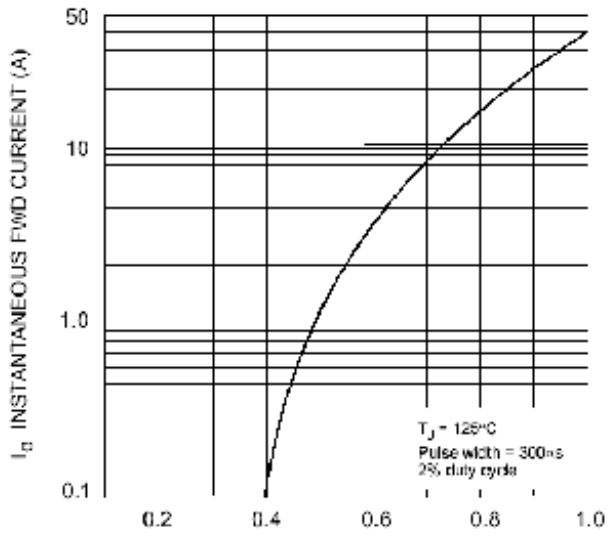


Fig. 2 Typical Forward Characteristics

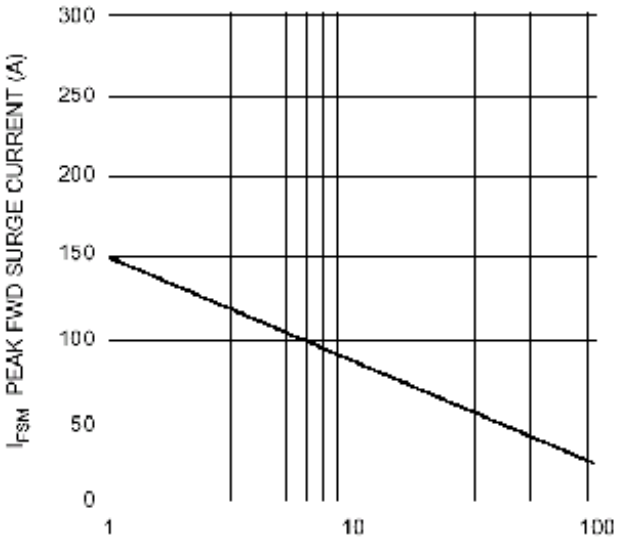


Fig. 3 Max Non-Repetitive Surge Current

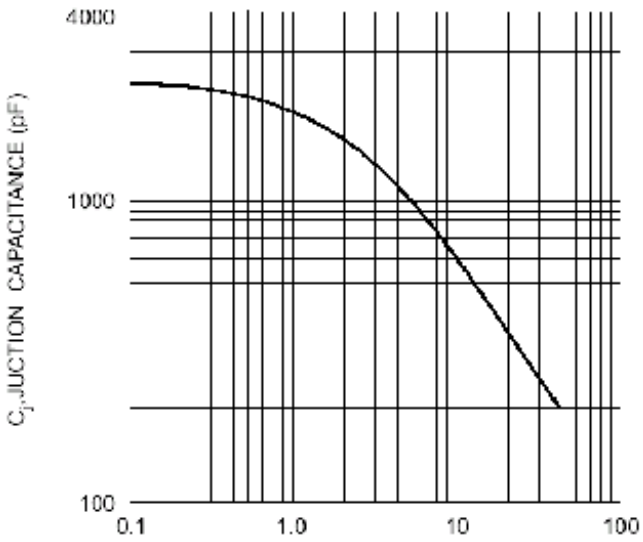


Fig. 4 Typical Junction Capacitance

NOTE:

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. Please do not exceed the absolute maximum ratings of the device when circuit designing.
2. When installing the heat sink, please pay attention to the torsional moment and the smoothness of the heat sink.
3. MOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. Shenzhen Minos reserves the right to make changes in this specification sheet and is subject to change withoutprior notice.

CONTACT:

深圳市迈诺斯科技有限公司（总部）

地址：深圳市福田区华富街道田面社区深南中路4026号田面城市大厦22B-22C

邮编：518025

电话：0755-83273777